

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

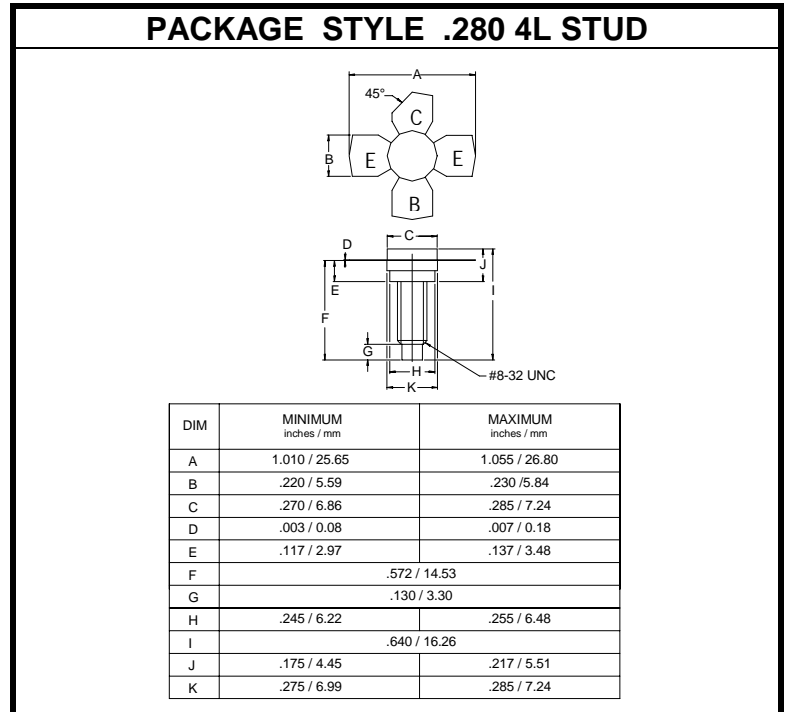
The **ASI BLX93A** is Designed for transmitting applications in class-A, B or C with a supply voltage up to 28 V

FEATURES:

- High Gain - 9.0 dB
- **Omnigold™** Metallization System
- Common Emitter

MAXIMUM RATINGS

I_C	1.0 A
V_{CB}	65 V
P_{DISS}	12.5 W @ T _C = 25 °C
T_J	-65 to +200 °C
T_{STG}	-65 to +150 °C
θ_{JC}	9.8 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 10 mA	65			V
BV_{CES}	I _C = 10 mA	65			V
BV_{CEO}	I _C = 25 mA	33			V
BV_{EBO}	I _E = 1.0 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	10			---
F_T	V _{CE} = 5.0 V I _C = 200 mA		1.2		GHz
C_c	V _{CB} = 10 V f = 1.0 MHz		14		pF
C_e	V _{EB} = 0 V f = 1.0 MHz		60		pF
P_G	V _{CE} = 28 V P _{OUT} = 7.0 W f = 470 MHz	8.5	9.0		dB
η_c		60	75		%